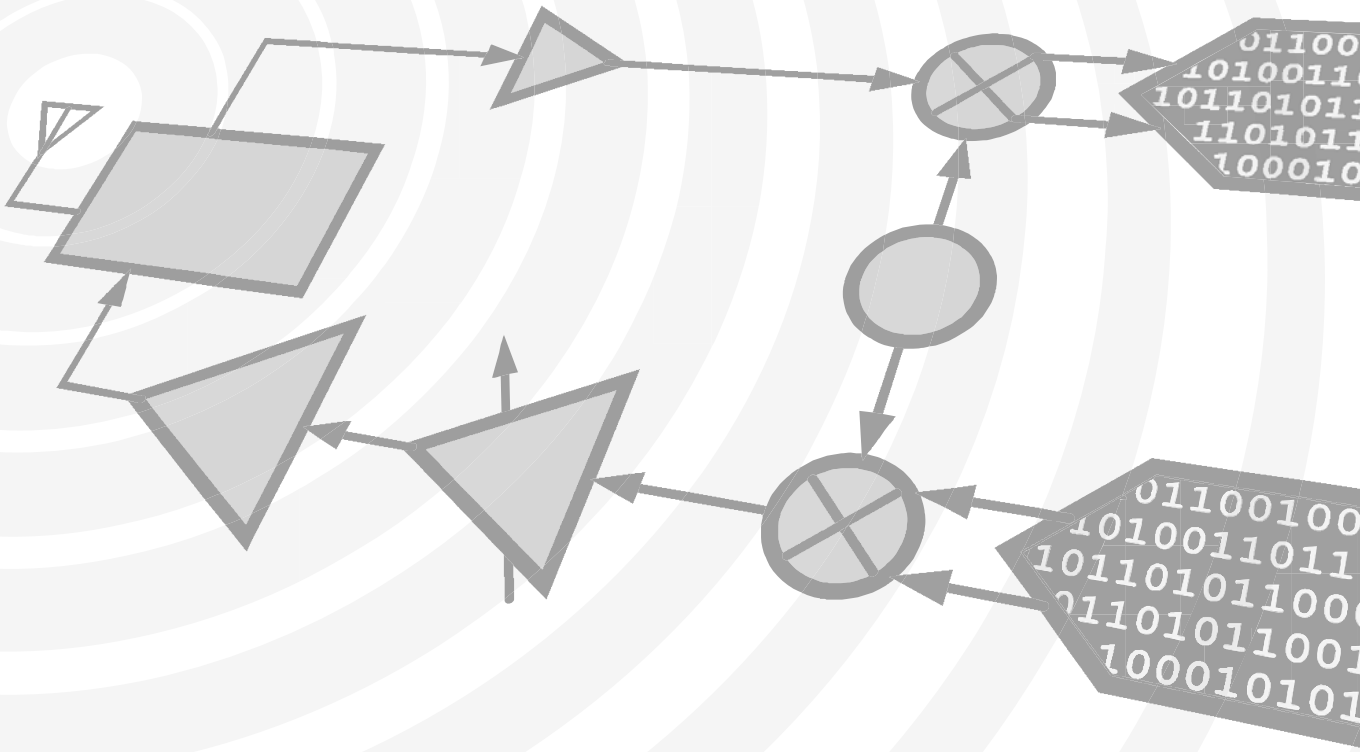
ANALOG DEVICES

Hittite MICROWAVE PRODUCTS FROM ANALOG DEVICES

Analog Devices Welcomes Hittite Microwave Corporation

NO CONTENT ON THE ATTACHED DOCUMENT HAS CHANGED



www.analog.com

www.hittite.com

THIS PAGE INTENTIONALLY LEFT BLANK

v02.1212

HMC6980

WIDEBAND POWER AMPLIFIER MODULE, 0.01 - 20 GHZ

Features

Gain: 12 dB

P1dB Output Power: +28 dBm

Regulated Supply and Bias Sequencing

Hermetically Sealed Module

Field Replaceable SMA connectors

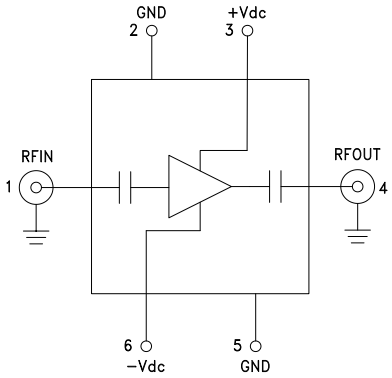
0 to +85 ˚C Operating Temperature

Typical Applications

The HMC6980 Wideband PA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation
- Fiber Optics

Functional Diagram



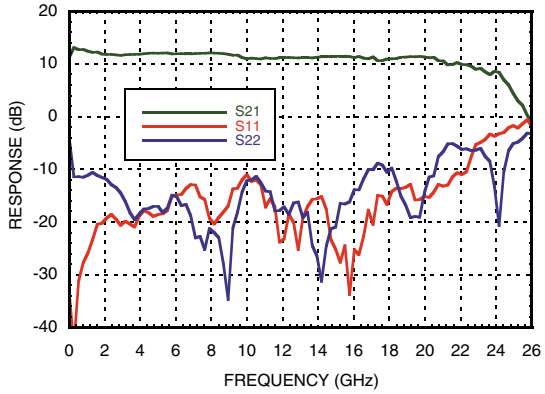
General Description

The HMC6980 is a GaAs MMIC PHEMT Power Amplifier in a miniature, hermetic module with replaceable SMA connectors which operates between 0.01 GHz and 20 GHz. The amplifier provides 12 dB of gain, up to +36 dBm output IP3 and up to +28 dBm of output power at 1 dB gain compression. Gain flatness is excellent from 2 - 18 GHz making the HMC6980 ideal for EW, ECM, Radar, Fiber Optic and test equipment applications. The wideband amplifier I/Os are internally matched to 50 Ohms and are DC blocked. Integrated voltage regulators allow for flexible biasing of both the negative and positive supply pins, while internal bias sequencing circuitry assures robust operation.

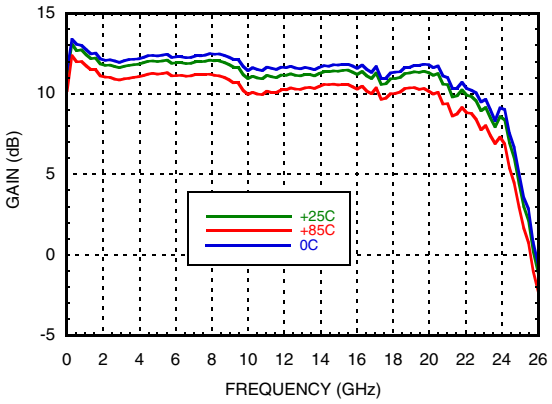
Electrical Specifications, T_A = +25° C, +Vdc = +11V, -Vdc = -3V to -12V

Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range		0.5 - 6.0			6 - 12			12 - 20		GHz
Gain	9	12		9	11		8	11		dB
Gain Flatness		±0.3			±0.3			±0.5		dB
Gain Variation Over Temperature		0.02			0.02			0.02		dB/ °C
Noise Figure		4.5			3.5			5.0		dB
Input Return Loss		25			17			15		dB
Output Return Loss		20			17			12		dB
Output Power for 1 dB Compression (P1dB)	25	28		24	27		20	24		dBm
Saturated Output Power (Psat)		29			27.5			26		dBm
Output Third Order Intercept (IP3)		36			34			29		dBm
Positive Supply Current (+IDC)		345			345			345		mA
Negative Supply Current (-IDC)		-5			-5			-5		mA

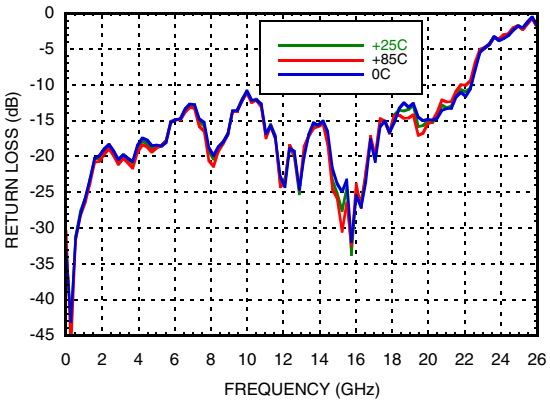
Gain & Return Loss



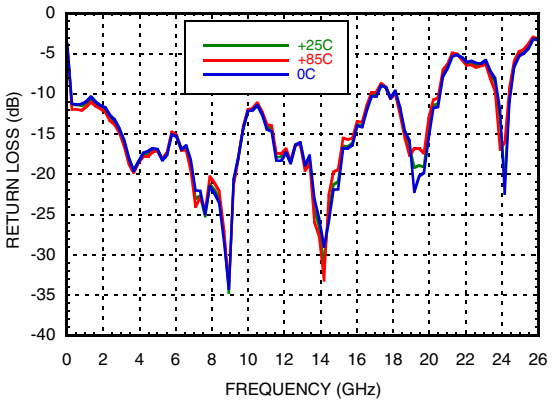
Gain vs. Temperature



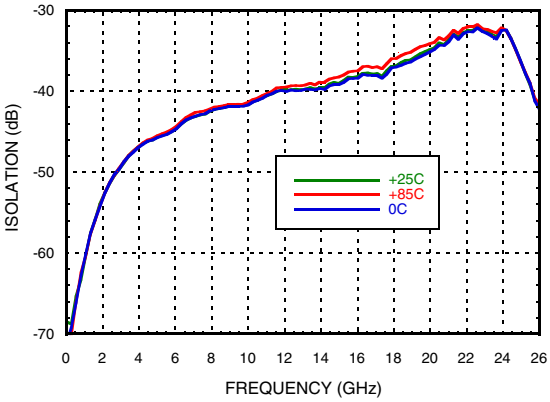
Input Return Loss vs. Temperature



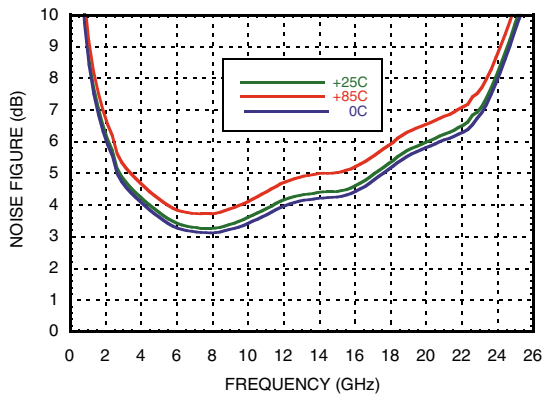
Output Return Loss vs. Temperature



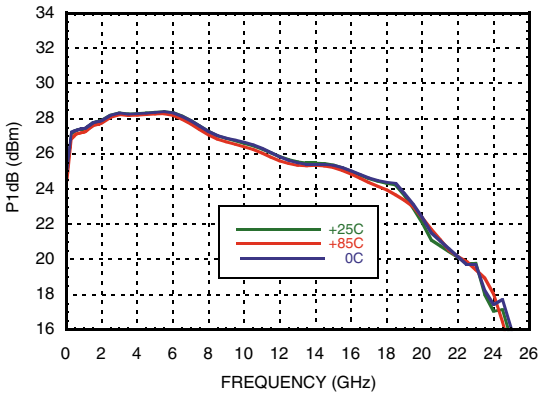
Reverse Isolation vs. Temperature



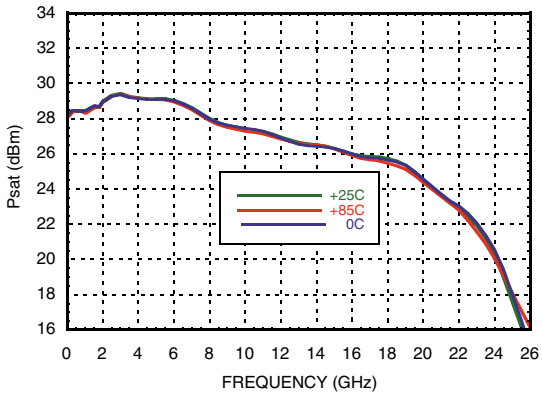
Noise Figure vs. Temperature



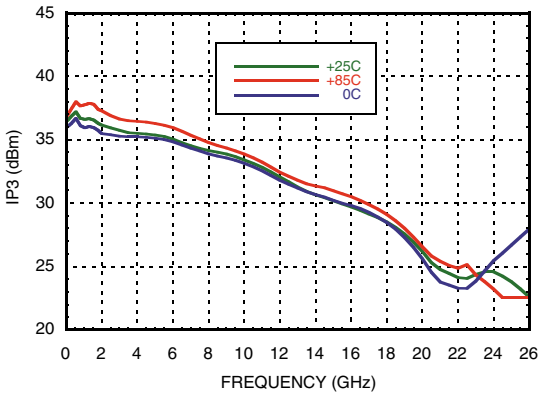
P1dB vs. Temperature



Psat vs. Temperature



Output IP3 vs. Temperature

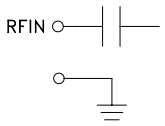
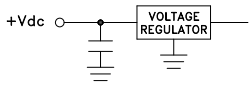
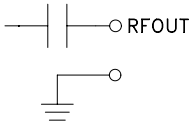
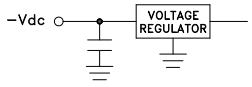


Absolute Maximum Ratings

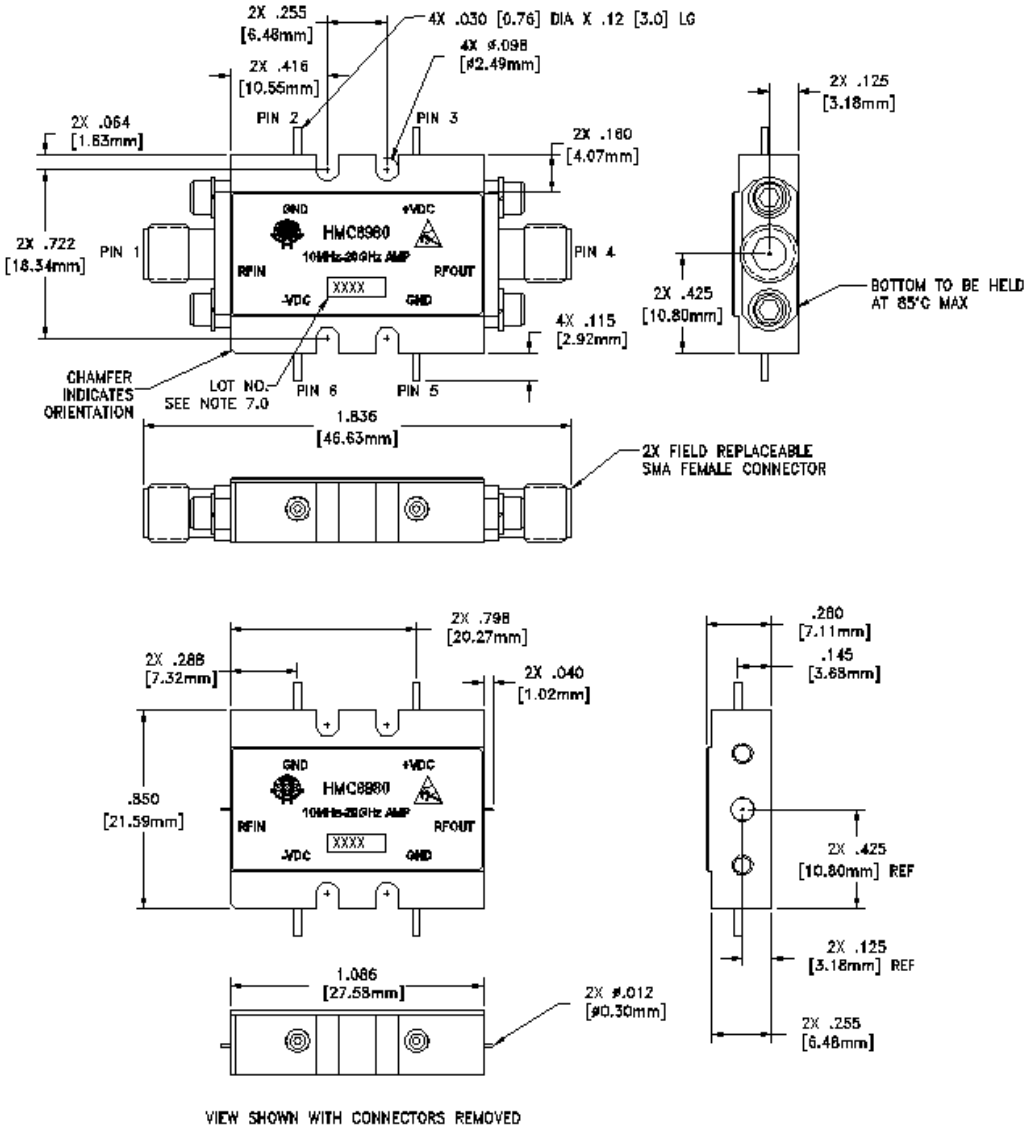
Positive Bias Supply Voltage (+Vdc)	+12V Max
Negative Bias Supply (-Vdc)	-16V Min.
Maximum RF Input Power (CW)	+27 dBm
Storage Temperature	-65 to +150 °C
Operating Temperature	0 to +85 °C
ESD Sensitivity (HBM)	Class 1A

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	RFIN & RF Ground	RF input connector, SMA female, field replaceable. This pin is AC coupled and matched to 50 Ohms.	
2, 5	GND	Power supply ground.	
3	+Vdc	Positive power supply voltage for the amplifier.	
4	RFOUT & RF Ground	RF output connector, SMA female. This pin is AC coupled and matched to 50 Ohms.	
6	-Vdc	Negative power supply voltage for the amplifier	

Outline Drawing



Package Information

Package Type	C-10B
Package Weight [1]	23.1 gms [2]
Spacer Weight	N/A

[1] Includes the connectors

[2] ±1 gms Tolerance

NOTES:

1. PACKAGE, LEADS, COVER MATERIAL: KOVAR™
2. SPACER MATERIAL: ALUMINUM
3. PLATING: ELECTROLYTIC GOLD 50 MICROINCHES MIN., OVER ELECTROLYTIC NICKEL 75 MICROINCHES MIN.
4. ALL DIMENSIONS ARE IN INCHES [MILLIMETERS].
5. TOLERANCES ±0.010 [0.25] UNLESS OTHERWISE SPECIFIED.
6. FIELD REPLACEABLE SMA CONNECTORS. TENSOLITE 5602 - 5CCSF OR EQUIVALENT.

Notes: